

Amendments to the Specification:

Please replace paragraph [0014] with the following amended paragraph:

5 Please refer to FIG. 1, which is a structure diagram illustrating a light emitting diode 10 in accordance with a first embodiment of the present invention. The wavelength associated with light emitted from the LED 10 is 468nm. The LED 10 has an insulating substrate 12 made of sapphire (Al_2O_3), a buffer layer 14 formed on the insulating substrate 12, an n-type contact layer 16 formed on the buffer layer 14, an n-type cladding layer 17 formed on a first surface region of the n-type contact layer 16.
10 10 a multiple quantum well light emitting layer 18 formed on the n-type cladding layer 17 a first surface region of the n-type contact layer 16, a p-type cladding layer 20 formed on the multiple quantum well light emitting layer 18, a p-type contact layer 22 formed on the p-type cladding layer 20, a dual dopant contact layer 24 formed on the p-type contact layer 22, a transparent conductive oxide layer 26 formed on the dual
15 dopant contact layer 24, a p-type electrode 28 formed on the transparent conductive oxide layer 26, and an n-type electrode 30 formed on a second surface region of the n-type contact layer 16.

Please replace paragraph [0019] with the following amended paragraph:

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The n-type conductive substrate 42 is made of one material selected from a material group consisting of GaN, SiC, Si, AlN, ZnO, MgO, GaP, GaAs, and Ge. The above-mentioned insulating substrate 12 is made of one semiconductor material selected from a material group consisting of sapphire, LiGaO_2 , and LiAlO_2 . The
25 above-mentioned buffer layer 14 is made of AlInGaN-based material or II-nitride-based material. The above-mentioned n-type cladding layer 17 comprises $\text{Al}_x\text{Ga}_{1-x}\text{N}$, and $0 \leq x \leq 1$. The above-mentioned multiple quantum well light emitting layer 18 comprises r InGaN quantum wells and (r+1) InGaN barriers so that both sides of each InGaN quantum well is sandwiched in between two InGaN barriers. Please
30 note that r is not less than 1, each InGaN quantum well is formed by $\text{In}_e\text{Ga}_{1-e}\text{N}$, and each InGaN barrier is formed by $\text{In}_f\text{Ga}_{1-f}\text{N}$ ($0 \leq f < e \leq 1$). The above-mentioned

p-type cladding layer 20 comprises $\text{Al}_z\text{Ga}_{1-z}\text{N}$, wherein $0 \leq z \leq 1$. The above-mentioned transparent conductive oxide layer 26 is made of one semiconductor material selected from a material group consisting of Indium-tin oxide (ITO), Cadmium-tin oxide, Antimony-tin oxide (ATO), Zinc oxide (ZnO), and Zinc-tin oxide.

- 5 The above-mentioned dual dopant contact layer 24 is made of GaN-based material. The above-mentioned n-type dopant is made of one material selected from a material group consisting of Si, Ge, Sn, Te, O, S, and C, and the p-type dopant is made of one material selected from a material group consisting of Mg, Zn, Be, and Ca.